Vishay Semiconductors





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AAP Gen 7 (TO-240AA)

PRIMARY CHARACTERISTICS				
I _{F(AV)} 100 A				
V _R	45 V			
Package	AAP Gen 7 (TO-240AA)			
Circuit configuration Two diodes doubler circuit				

MECHANICAL DESCRIPTION

The AAP Gen 7, new generation of ADD-A-PAK module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- 150 °C T_J operation
- Low forward voltage drop
- High frequency operation
- Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- High surge capability
- Easy mounting on heatsink

ELECTRICAL DESCRIPTION / APPLICATIONS

The VS-VSKDS200/045 Schottky rectifier doubler module has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in high current switching power supplies, plating power supplies, UPS systems, converters, freewheeling diodes, welding, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS	UNITS					
I _{F(AV)}	Rectangular waveform	100	A				
V _{RRM}		45	V				
I _{FSM}	t _p = 5 μs sine	12 800	A				
V _F	100 A _{pk} , T _J = 125 °C	0.73	V				
TJ	Range	-55 to +150	°C				

VOLTAGE RATINGS						
PARAMETER	SYMBOL	VS-VSKDS200/045	UNITS			
Maximum DC reverse voltage	V _R	45	V			
Maximum working peak reverse voltage	V _{RWM}	40	v			

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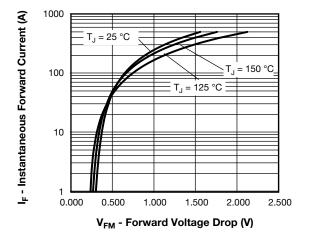
ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDI	VALUES	UNITS	
Maximum average forward current per leg	I _{F(AV)}	$I_{F(AV)}$ 50 % duty cycle at T _C = 91 °C, rectangular waveform		100	
Maximum peak one cycle non-repetitive surge current	I _{FSM}	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with	12 800	А
		10 ms sine or 6 ms rect. pulse	rated V_{RRM} applied	1700	
Non-repetitive avalanche energy	E _{AS}	$T_J = 25 \text{ °C}, I_{AS} = 19 \text{ A}, L = 1 \text{ mH}$ 1		180	mJ
Repetitive avalanche current	I _{AR}	$I_{AR} \qquad \begin{array}{c} \mbox{Current decaying linearly to zero in 1 } \mu s \\ \mbox{Frequency limited by } T_J \mbox{ maximum } V_A = 1.5 \ x \ V_R \ typical \end{array}$		15	А

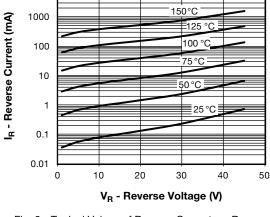
ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CO	VALUES	UNITS	
		100 A	T.I = 25 °C	0.67	V
	V _{FM}	200 A	1j=25 C	0.92	
Maximum forward voltage drop		100 A	T 405.00	0.73	
		200 A	T _J = 125 °C	1.14	
Maximum roverse leakage ourrent	I _{RM}	T _J = 25 °C	$V_{\rm B}$ = Rated $V_{\rm B}$	10	mA
Maximum reverse leakage current		T _J = 125 °C	$v_{\rm R} = nateu v_{\rm R}$	800	
Maximum junction capacitance	CT	$V_R = 5 V_{DC}$ (test signal range 100 kHz to 1 MHz), 25 °C		5200	pF
Typical series inductance	L _S	Measured lead to lead 5 mm from package body		7.0	nH
Maximum voltage rate of change	dV/dt	Rated V _R	10 000	V/µs	
Maximum RMS insulation voltage	V _{INS}	50 Hz		3000 (1 min) 3600 (1 s)	V

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	9	T _J , T _{Stg}		-55 to +150	°C
Maximum thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.52	°C/W
Typical thermal resistance, case to heatsink per module		R _{thCS}		0.1	0/10
Approximate weight				75	g
Approximate weight				2.7	oz.
Mounting torque ± 10 % to heatsink			A mounting compound is recommended and the torque should be rechecked after a period of 3 h to allow for the	4	Nm
			should be rechecked after a period of 3 h to allow for the spread of the compound.	3	
Case style			JEDEC®	TO-240AA co	mpatible



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Fig. 1 - Maximum Forward Voltage Drop Characteristics



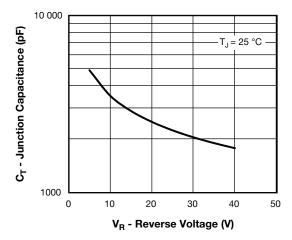
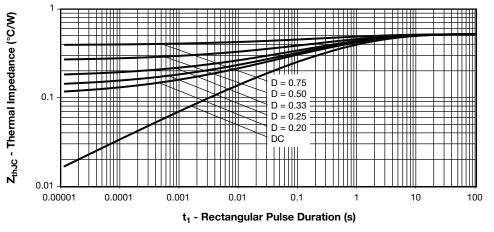


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



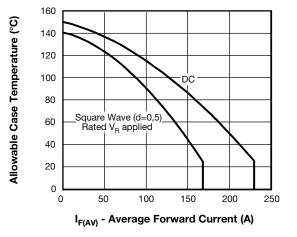


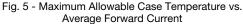
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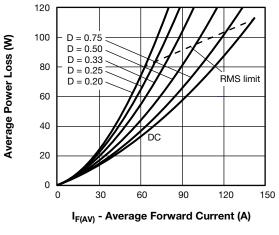
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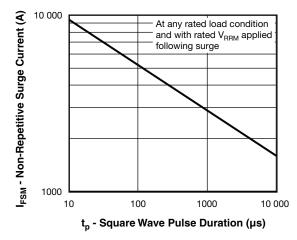


Fig. 7 - Maximum Non-Repetitive Surge Current

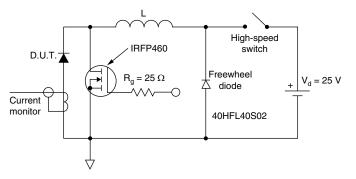


Fig. 8 - Unclamped Inductive Test Circuit

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ x \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ x \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \ - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{80} \ \% \ \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

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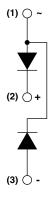
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ORDERING INFORMATION TABLE

Device code	vs-vs	KD	S	20	0	1	045
		2	3	4	5		6
	1 - 2 - 3 - 4 - 5 - 6 -	Circ KD S = Ave Pro	cuit conf = ADD-, Schottk erage cu duct silio		n: 2 diode ing (20 itificatio	es doub = 200 A n	ler circuit

CIRCUIT CONFIGURATION



LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95369

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ADD-A-PAK Generation VII - Diode

DIMENSIONS in millimeters (inches)





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